	Application No.	Applicant(s)	
Notice of Allowability	10/667,589 Examiner	TSAI, JUNG-HUI Art Unit	Our
	Thanh V. Pham	2823	
The MAILING DATE of this communication apperall claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this apport or other appropriate communication IGHTS. This application is subject to	olication. If not included will be mailed in due cou	ırse. THIS
1. This communication is responsive to			
2. The allowed claim(s) is/are <u>1-15</u> .			
3. 🗵 The drawings filed on <u>09/23/2003</u> are accepted by the Exa	miner.		
4. Acknowledgment is made of a claim for foreign priority unall blank blank collaboration and all blank collaboration and collaboration an	e been received. been received in Application Nocuments have been received in this rece	complying with the required S AMENDMENT or NOT attion is deficient. 948) attached Office action of the band). The nust be submitted. Not the band is the submitted.	rements
 Attachment(s) 1. ☑ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☐ Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date	5. Notice of Informal P 6. Interview Summary Paper No./Mail Dat 7. Examiner's Amendo 8. Examiner's Stateme 9. Other	(PTO-413), te ment/Comment	, and the second

EXAMINER'S AMENDMENT

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Mr. Richard Fichter on 04/21/2005.

The application has been amended as follows:

In claim 1, from line 2 to line 11, delete "comprises a semiconductor substrate, a buffer layer on said semiconductor substrate, a non-doped strain layer on said buffer layer, a first non-doped spacer layer on said non-doped strain layer, a δ -doped carrier supplying layer on said first non-doped spacer layer, a second non-doped spacer layer on said δ -doped carrier supplying layer, a n-doped semiconductor layer on said second non-doped spacer layer, a p⁺-doped semiconductor layer on said n-doped semiconductor layer, and a n⁺-doped semiconductor covering layer over the aforementioned p⁺-doped semiconductor layer. In" and insert --comprising

- a semiconductor substrate;
- a buffer layer on said semiconductor substrate;
- a non-doped strain layer on said buffer layer;
- a first non-doped spacer layer on said non-doped strain layer;
- a δ -doped carrier supplying layer on said first non-doped spacer layer;
- a second non-doped spacer layer on said δ -doped carrier supplying layer;

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an n-doped semiconductor layer on said second non-doped spacer layer;

a p*-doped semiconductor layer on said n-doped semiconductor layer; and

an n*-doped semiconductor covering layer over the aforementioned p*-doped

semiconductor layer; wherein, -- instead.

In claim 2, line 2 to line 3, delete "layer, an additional non-doped spacer layer on said additional δ -doped carrier supplying layer, wherein" and insert --layer; an additional non-doped spacer layer on said additional δ -doped carrier supplying layer; therefore, -- instead.

- 2. The following is an examiner's statement of reasons for allowance: the cited prior art, individually or in combination, does not disclose or suggest all of the claimed elements in the present application, for examples, US Pub. 2003/0017683 provides a pHEMT having most of the explanation but lacks the δ -doped for the carrier layer and the n-p-n layers in the claimed sequential layers. US Pub. 2004/0157353 has the n-p-n layers but lacks the δ -doped layer in the epitaxial multi layers and most mention to pHEMT. US Pub. 2004/0155261 and 2004/0119090 teach the epitaxial multi layers but the sequential layers arrange different from the claimed invention and also lacks the n-p-n layers. The combination could not be made because of the uniqueness of each design.
- 3. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

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4. Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Thanh V. Pham whose telephone number is 703-308-

2543. The examiner can normally be reached on M-T (6:30-5:00).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

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supervisor, Olik Chaudhuri can be reached on 703-306-2794. The fax phone number

for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the

Patent Application Information Retrieval (PAIR) system. Status information for

published applications may be obtained from either Private PAIR or Public PAIR.

Status information for unpublished applications is available through Private PAIR only.

For more information about the PAIR system, see http://pair-direct.uspto.gov. Should

you have questions on access to the Private PAIR system, contact the Electronic

Business Center (EBC) at 866-217-9197 (toll-free).

TVP

04/21/2005